

# **HD74ALVCH162827**

# 20-bit Buffers / Drivers with 3-state Outputs

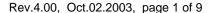
REJ03D0042-0400Z (Previous ADE-205-188B (Z) ) Rev.4.00 Oct.02.2003

#### **Description**

The HD74ALVCH162827 is composed of two 10-bit sections with separate output enable signals. For either 10-bit buffer section, the two output enable  $(1\overline{OE1} \text{ and } 1\overline{OE2} \text{ or } 2\overline{OE1} \text{ and } 2\overline{OE2})$  inputs must both be low for the corresponding Y outputs to be active. If either output enable input is high, the outputs of that 10-bit buffer section are in the high impedance state. Active bus hold circuitry is provided to hold unused or floating data inputs at a valid logic level. All outputs, which are designed to sink up to 12 mA, include  $26~\Omega$  resistors to reduce overshoot and undershoot.

#### **Features**

- $V_{CC} = 2.3 \text{ V to } 3.6 \text{ V}$
- Typical  $V_{OL}$  ground bounce < 0.8 V (@ $V_{CC} = 3.3$  V, Ta = 25°C)
- Typical  $V_{OH}$  undershoot > 2.0 V (@ $V_{CC}$  = 3.3 V, Ta = 25°C)
- High output current  $\pm 12$  mA (@V<sub>CC</sub> = 3.0 V)
- Bus hold on data inputs eliminates the need for external pullup / pulldown resistors
- All outputs have equivalent  $26 \Omega$  series resistors, so no external resistors are required.





#### **Function Table**

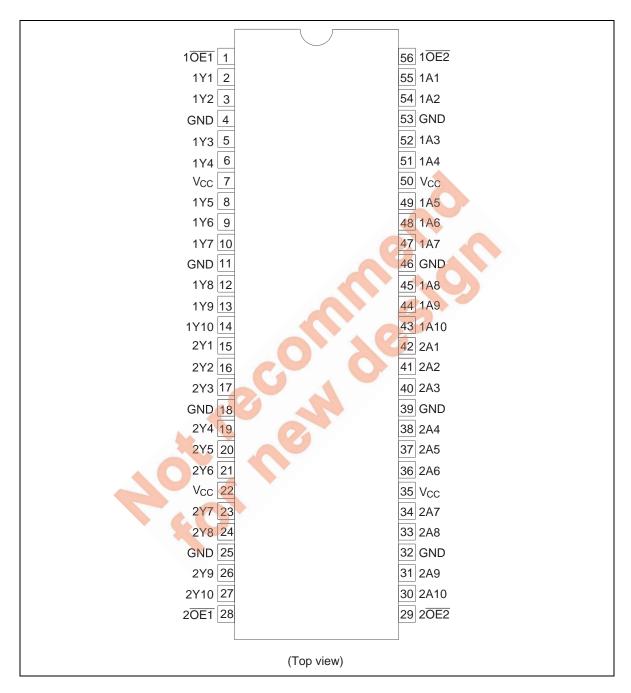
Inputs			Output Y	
OE1	OE2	Α		
L	L	L	L	
L	L	Н	Н	
Н	Х	Х	Z	
X	Н	Х	Z	

H : High level L : Low level

X : Immaterial

Z : High impedance

### **Pin Arrangement**



# **Absolute Maximum Ratings**

Item	Symbol	Ratings	Unit	Conditions
Supply voltage	V <sub>CC</sub>	-0.5 to 4.6	V	
Input voltage *1	Vı	-0.5 to 4.6	V	
Output voltage *1, 2	Vo	-0.5 to V <sub>CC</sub> +0.5	V	
Input clamp current	I <sub>IK</sub>	<b>–</b> 50	mA	V <sub>I</sub> < 0
Output clamp current	I <sub>OK</sub>	±50	mA	$V_O < 0$ or $V_O > V_{CC}$
Continuous output current	I <sub>O</sub>	±50	mA	$V_O = 0$ to $V_{CC}$
V <sub>CC</sub> , GND current / pin	I <sub>CC</sub> or I <sub>GND</sub>	±100	mA	
Maximum power dissipation at Ta = 55°C (in still air) *3	P <sub>T</sub>	1	W	TSSOP
Storage temperature	Tstg	-65 to 150	°C	

Notes: Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute maximum rated conditions for extended periods may affect device reliability.

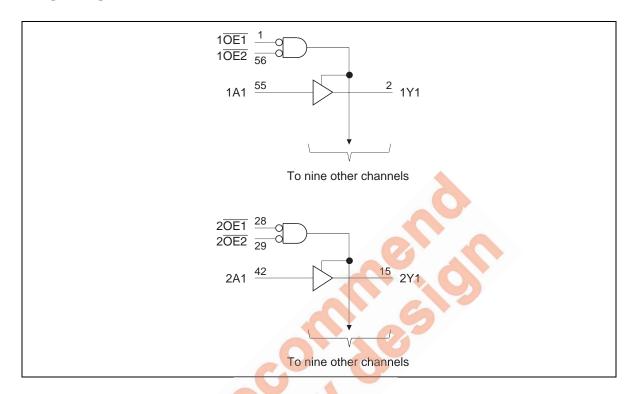
- 1. The input and output negative voltage ratings may be exceeded if the input and output clamp current ratings are observed.
- 2. This value is limited to 4.6 V maximum.
- 3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils.

### **Recommended Operating Conditions**

Item	Symbol	Min	Max	Unit	Conditions
Supply voltage	V <sub>CC</sub>	2.3	3.6	V	
Input voltage	VI	0	V <sub>CC</sub>	V	
Output voltage	Vo	0	V <sub>CC</sub>	V	
High level output current	Гон	_	-6	mA	V <sub>CC</sub> = 2.3 V
		_	-8		$V_{CC} = 2.7 \text{ V}$
		_	-12		$V_{CC} = 3.0 \text{ V}$
Low level output current	loL	_	6	mA	V <sub>CC</sub> = 2.3 V
		_	8		$V_{CC} = 2.7 \text{ V}$
		_	12		$V_{CC} = 3.0 \text{ V}$
Input transition rise or fal	I rate Δt / Δv	0	10	ns / V	
Operating temperature	Та	-40	85	°C	

Note: Unused control inputs must be held high or low to prevent them from floating.

# Logic Diagram



### **Electrical Characteristics**

 $(Ta = -40 \text{ to } 85^{\circ}C)$ 

Item	Symbol	<b>V</b> <sub>CC</sub> <b>(V)</b> *1	Min	Max	Unit	Test Conditions
Input voltage	V <sub>IH</sub>	2.3 to 2.7	1.7	_	V	
		2.7 to 3.6	2.0	_	_	
	V <sub>IL</sub>	2.3 to 2.7	_	0.7	_	
		2.7 to 3.6	_	8.0	_	
Output voltage	V <sub>OH</sub>	Min to Max	V <sub>CC</sub> -0.2	_	V	$I_{OH} = -100  \mu A$
		2.3	1.9	_	_	I <sub>OH</sub> = -4 mA, V <sub>IH</sub> = 1.7 V
		2.3	1.7	_		I <sub>OH</sub> = -6 mA, V <sub>IH</sub> = 1.7 V
		3.0	2.4	_	1	$I_{OH} = -6 \text{ mA}, V_{IH} = 2.0 \text{ V}$
		2.7	2.0	-		$I_{OH} = -8 \text{ mA}, V_{IH} = 2.0 \text{ V}$
		3.0	2.0	-	9	$I_{OH} = -12 \text{ mA}, V_{IH} = 2.0 \text{ V}$
	V <sub>OL</sub>	Min to Max	_	0.2	-	I <sub>OL</sub> = 100 μA
		2.3	- 4	0.4		$I_{OL} = 4 \text{ mA}, V_{IL} = 0.7 \text{ V}$
		2.3	-	0.55	4	$I_{OL}' = 6 \text{ mA}, V_{IL} = 0.7 \text{ V}$
		3.0	94.	0.55	5)	$I_{OL} = 6 \text{ mA}, V_{IL} = 0.8 \text{ V}$
		2.7		0.6		$I_{OL} = 8 \text{ mA}, V_{IL} = 0.8 \text{ V}$
		3.0	- 4	0.8	_	I <sub>OL</sub> = 12 mA, V <sub>IL</sub> = 0.8 V
Input current	I <sub>IN</sub>	3.6	-16	±5	μΑ	V <sub>IN</sub> = V <sub>CC</sub> or GND
	I <sub>IN (hold)</sub>	2.3	45	_	_	V <sub>IN</sub> = 0.7 V
	N.	2.3	-45	_		V <sub>IN</sub> = 1.7 V
		3.0	75	_		V <sub>IN</sub> = 0.8 V
		3.0	<del>-</del> 75	_		V <sub>IN</sub> = 2.0 V
	10	3.6	_	±500	_	V <sub>IN</sub> = 0 to 3.6 V
Off state output current *2	loz	3.6	_	±10	μΑ	$V_{OUT} = V_{CC}$ or GND
Quiescent supply current	Icc	3.6	_	40	μΑ	$V_{IN} = V_{CC}$ or GND
	$\Delta I_{CC}$	3.0 to 3.6	_	750	μΑ	$V_{\text{IN}}$ = one input at (V <sub>CC</sub> -0.6) V, other inputs at V <sub>CC</sub> or GND

Notes: 1. For conditions shown as Min or Max, use the appropriate values under recommended operating conditions.

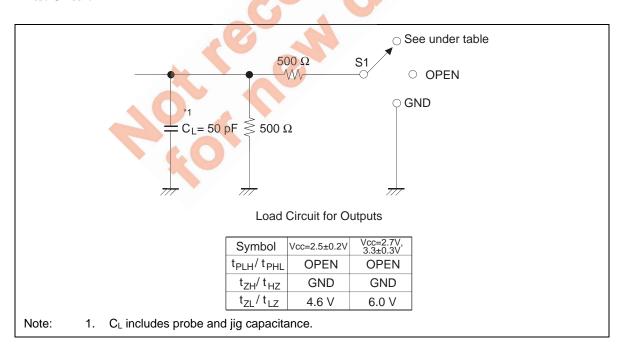
<sup>2.</sup> For I/O ports, the parameter  $I_{\text{OZ}}$  includes the input leakage current.

# **Switching Characteristics**

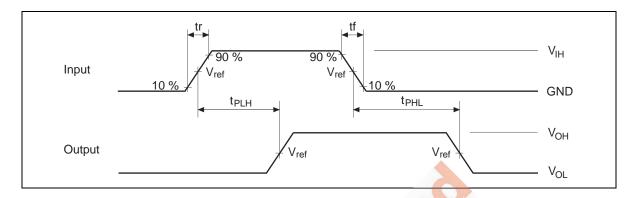
 $(Ta = -40 \text{ to } 85^{\circ}C)$ 

Item	Symbol	V <sub>CC</sub> (V)	Min	Тур	Max	Unit	FROM (input)	TO (output)
Propagation delay time	t <sub>PLH</sub>	2.5±0.2	1.0		4.4	ns	Α	Υ
	t <sub>PHL</sub>	2.7			4.4	_		
		3.3±0.3	1.0	_	3.8	_		
Output enable time	t <sub>zH</sub>	2.5±0.2	1.2		6.3	ns	ŌĒ	Υ
	t <sub>ZL</sub>	2.7	_	_	6.2			
		3.3±0.3	1.0	_	5.1	_		
Output disable time	$t_{HZ}$	2.5±0.2	1.9	_	5.9	ns	ŌĒ	Υ
	$t_{LZ}$	2.7	_	_	5.2	46		
		3.3±0.3	1.3	_	4.7			
Input capacitance	C <sub>IN</sub>	3.3		3.5		pF	Control inputs	
		3.3		6.0	7	•	Data inputs	
Output capacitance	Co	3.3	_	7.0		pF	outputs	

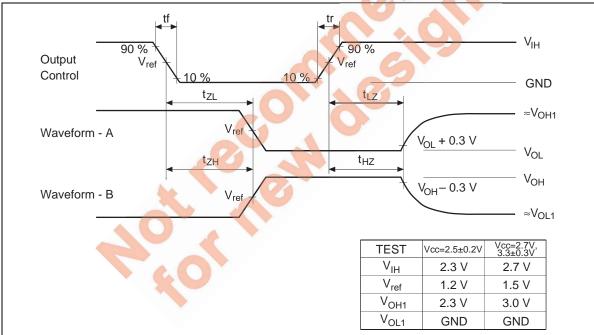
#### **Test Circuit**



#### Waveforms-1



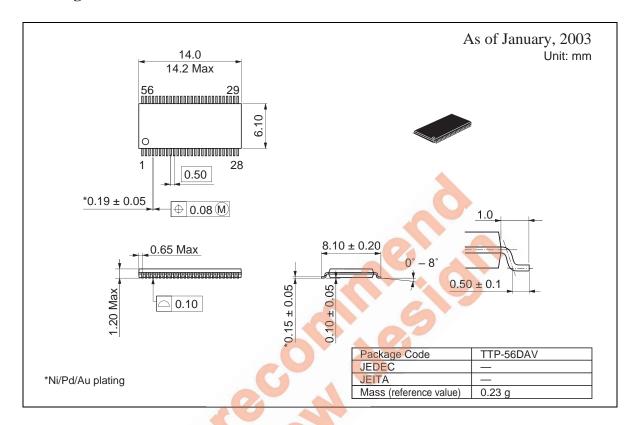
#### Waveforms-2



Notes:

- 1. All Notes: 1. Il input pulses are supplied by generators having the following characteristics : PRR  $\leq$  10 MHz, Zo = 50  $\Omega$ , tr  $\leq$  2.0 ns, tf  $\leq$  2.0 ns. (V<sub>CC</sub> = 2.5±0.2 V) PRR  $\leq$  10 MHz, Zo = 50  $\Omega$ , tr  $\leq$  2.5 ns, tf  $\leq$  2.5 ns. (V<sub>CC</sub> = 2.7 V, 3.3±0.3 V)
- 2. Waveform A is for an output with internal conditions such that the output is low except when disabled by the output control.
- 3. Waveform B is for an output with internal conditions such that the output is high except when disabled by the output control.
- 4. The output are measured one at a time with one transition per measurement.

# **Package Dimensions**



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